



Dual N-Channel 30-V (D-S) MOSFET with Schottky Diode

PRODUCT SUMMARY			
	V _{DS} (V)	r _{DS(on)} (Ω)	I _D (A)
Channel-1	30	0.011 @ V _{GS} = 10 V	10
		0.016 @ V _{GS} = 4.5 V	8.2
Channel-2		0.0085 @ V _{GS} = 10 V	14
		0.0095 @ V _{GS} = 4.5 V	13

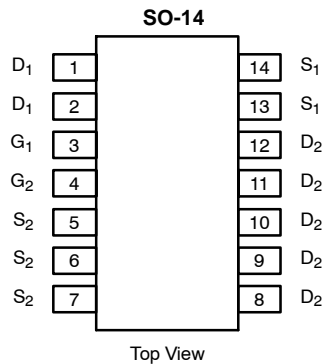
SCHOTTKY PRODUCT SUMMARY		
V _{DS} (V)	V _{SD} (V) Diode Forward Voltage	I _F (A)
30	0.53 V @ 3 A	2.0

FEATURES

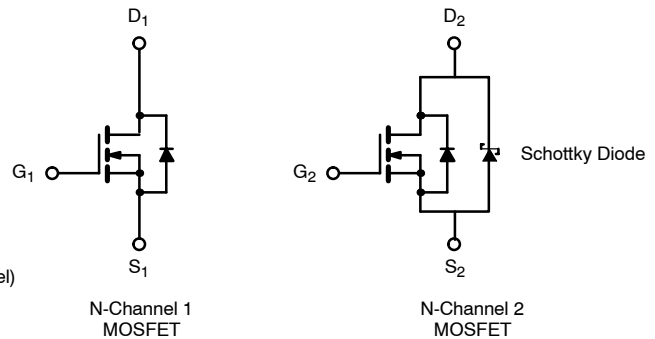
- TrenchFET® Power MOSFET
- 100% R_g Tested

APPLICATIONS

- DC/DC Converters
 - Game Stations
 - Video Equipment



Ordering Information:
Si4310BDY—E3
Si4310BDY-T1—E3 (with Tape and Reel)



ABSOLUTE MAXIMUM RATINGS (T _A = 25 °C UNLESS OTHERWISE NOTED)							
Parameter	Symbol	Channel-1		Channel-2		Unit	
		10 secs	Steady State	10 secs	Steady State		
Drain-Source Voltage	V _{DS}	30				V	
Gate-Source Voltage	V _{GS}	± 20		± 20			
Continuous Drain Current (T _J = 150 °C) ^a	I _D	T _A = 25 °C	10	7.5	14	9.8	A
		T _A = 70 °C	8	6	11	7.8	
Pulsed Drain Current	I _{DM}	40		50		A	
Continuous Source Current (Diode Conduction) ^a	I _S	1.8	1.04	2.73	1.33		
Maximum Power Dissipation ^a	P _D	T _A = 25 °C	2	1.14	3.0	1.47	W
		T _A = 70 °C	1.28	0.73	1.9	0.94	
Operating Junction and Storage Temperature Range	T _J , T _{stg}	-55 to 150				°C	

THERMAL RESISTANCE RATINGS									
Parameter	Symbol	Channel-1		Channel-2		Schottky		Unit	
		Typ	Max	Typ	Max	Typ	Max		
Maximum Junction-to-Ambient ^a	t ≤ 10 sec	R _{thJA}	53	62.5	34	35	40	48	°C/W
	Steady-State		92	110	70	72	76	93	
Maximum Junction-to-Foot (Drain)	Steady-State	R _{thJF}	35	42	17	24	21	26	

Notes
a. Surface Mounted on 1" x 1" FR4 Board.

MOSFET SPECIFICATIONS (T_J = 25 °C UNLESS OTHERWISE NOTED).

Parameter	Symbol	Test Condition	Min	Typ ^a	Max	Unit		
Static								
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA	Ch-1	1.0		3.0	V	
			Ch-2	1.0		3.0		
Gate-Body Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ±20 V	Ch-1			100	nA	
			Ch-2			100		
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 30 V, V _{GS} = 0 V	Ch-1			1	μA	
			Ch-2			100		
		V _{DS} = 30 V, V _{GS} = 0 V, T _J = 85 °C	Ch-1			15		
			Ch-2			4000		
On-State Drain Current ^b	I _{D(on)}	V _{DS} = 5 V, V _{GS} = 10 V	Ch-1	20			A	
			Ch-2	30				
Drain-Source On-State Resistance ^b	r _{DS(on)}	V _{GS} = 10 V, I _D = 10 A	Ch-1		0.009	0.011	Ω	
		V _{GS} = 10 V, I _D = 14 A	Ch-2		0.0065	0.0085		
		V _{GS} = 4.5 V, I _D = 8.2 A	Ch-1		0.013	0.016		
		V _{GS} = 4.5 V, I _D = 13 A	Ch-2		0.0075	0.0095		
Forward Transconductance ^b	g _{fs}	V _{DS} = 15 V, I _D = 10 A	Ch-1		30		S	
		V _{DS} = 15 V, I _D = 14 A	Ch-2		60			
Diode Forward Voltage ^b	V _{SD}	I _S = 1.8 A, V _{GS} = 0 V	Ch-1		0.76	1.1	V	
		I _S = 2.73 A, V _{GS} = 0 V	Ch-2		0.485	0.53		
Dynamic^a								
Input Capacitance	C _{iss}	V _{DS} = 15 V, V _{GS} = 0 V, f = 1 MHz	Ch-1	790	1580	2370	pF	
			Ch-2	1530	3060	4590		
Output Capacitance	C _{oss}		Ch-1	145	290	435		
			Ch-2	300	600	900		
Reverse Transfer Capacitance	C _{rss}		Ch-1	70	140	210		
			Ch-2	115	225	340		
Total Gate Charge	Q _g		Channel-1 V _{DS} = 15 V, V _{GS} = 4.5 V, I _D = 10 A Channel-2 V _{DS} = 15 V, V _{GS} = 4.5 V, I _D = 14 A	Ch-1		12	18	nC
Gate-Source Charge	Q _{gs}			Ch-2		19	30	
				Ch-1		5.3		
Gate-Drain Charge	Q _{gd}			Ch-2		10		
		Ch-1			4.3			
Ch-2		5						
Gate Resistance	R _g	f = 1 MHz	Ch-1	0.90	1.8	2.7	Ω	
			Ch-2	0.3	0.95	1.4		
Turn-On Delay Time	t _{d(on)}		Ch-1		13	20	ns	
			Ch-2		17	26		
Rise Time	t _r		Channel-1 V _{DD} = 15 V, R _L = 15 Ω I _D ≅ 1 A, V _{GEN} = 10 V, R _G = 6 Ω	Ch-1		10		15
			Ch-2		12	20		
Turn-Off Delay Time	t _{d(off)}		Channel-2 V _{DD} = 15 V, R _L = 15 Ω I _D ≅ 1 A, V _{GEN} = 10 V, R _G = 6 Ω	Ch-1		33		50
			Ch-2		53	80		
Fall Time	t _f		Ch-1		10	15		
			Ch-2		17	26		
Source-Drain Reverse Recovery Time	t _{rr}	I _F = 1.8 A, di/dt = 100 A/μs	Ch-1		25	40		
		I _F = 2.73 A, di/dt = 100 μA/μs	Ch-2		31	50		

Notes

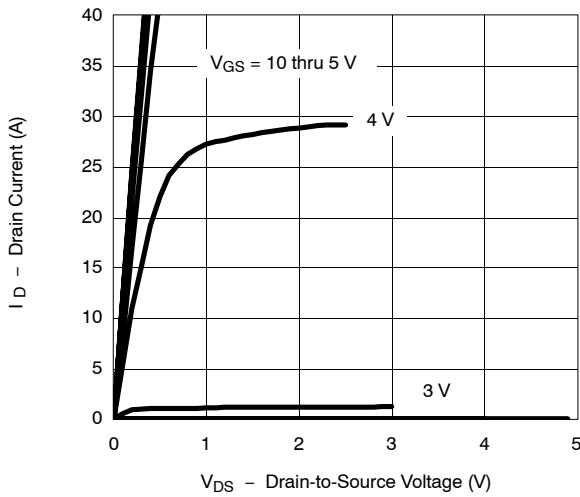
- a. Guaranteed by design, not subject to production testing.
b. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2%.



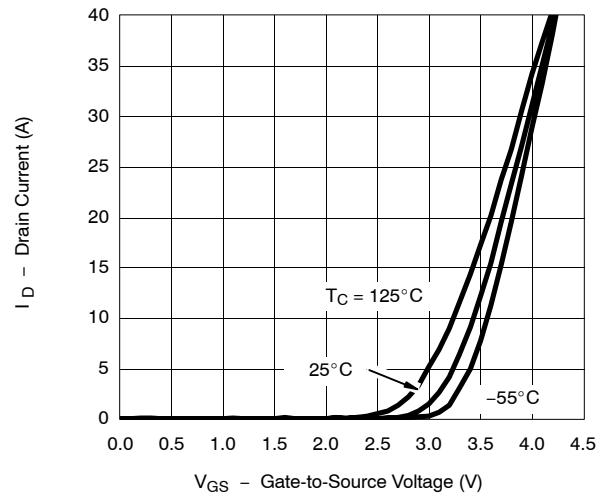
SCHOTTKY SPECIFICATIONS (T _J = 25°C UNLESS OTHERWISE NOTED)						
Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Forward Voltage Drop	V _F	I _F = 3 A		0.485	0.53	V
		I _F = 3 A, T _J = 125°C		0.42	0.42	
Maximum Reverse Leakage Current	I _{rm}	V _r = 30 V		0.008	0.100	mA
		V _r = 30 V, T _J = 75°C		0.4	5	
		V _r = -30 V, T _J = 125°C		6.5	20	
Junction Capacitance	C _T	V _r = 15 V		102		pF

TYPICAL CHARACTERISTICS (25°C UNLESS NOTED) CHANNEL-1

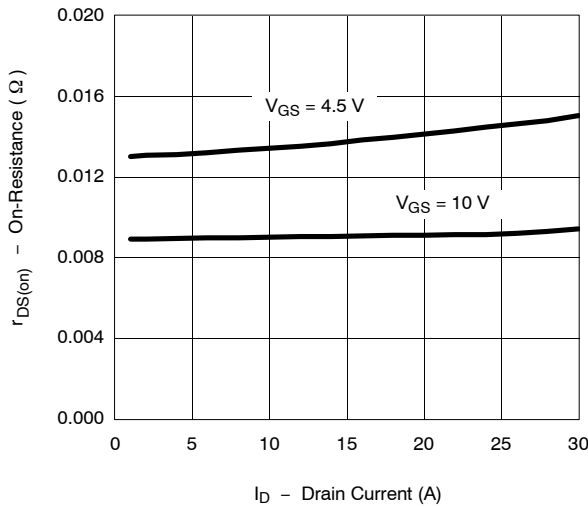
Output Characteristics



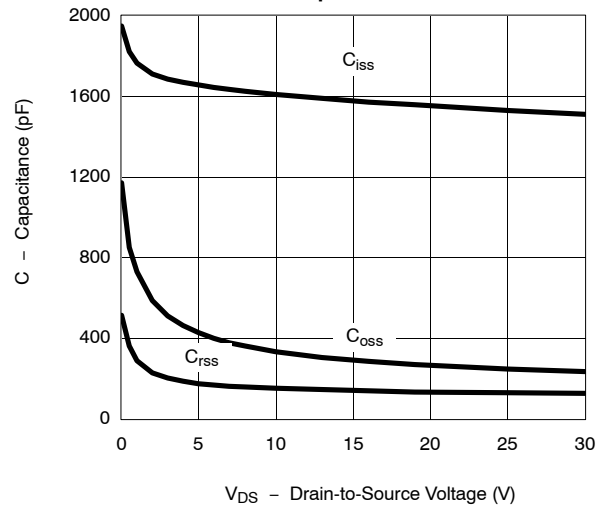
Transfer Characteristics



On-Resistance vs. Drain Current

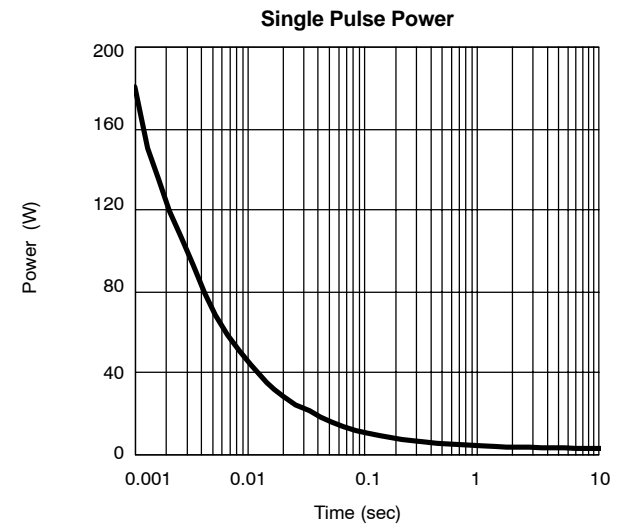
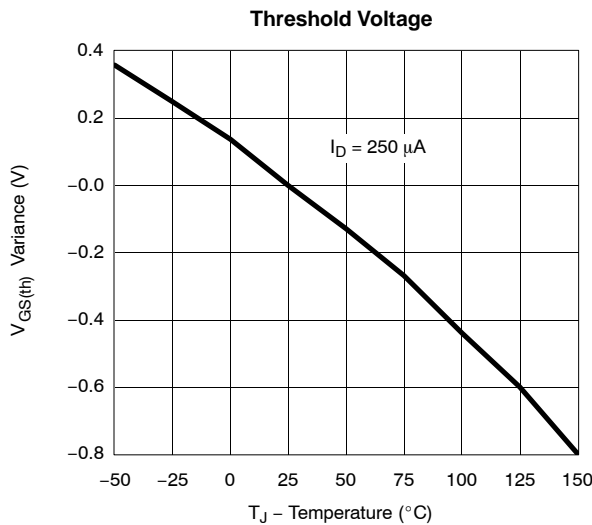
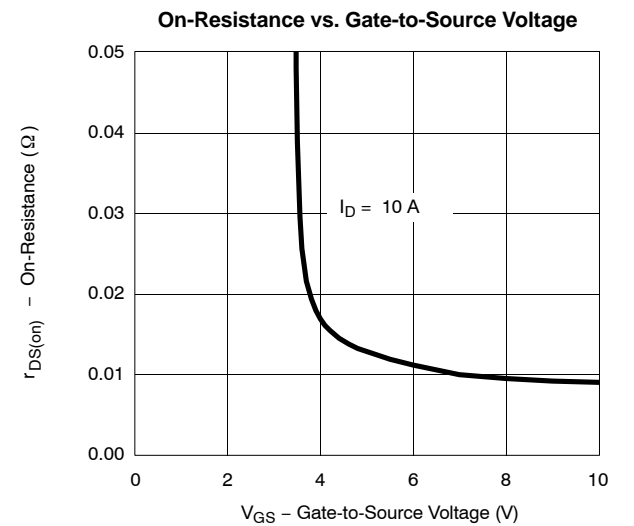
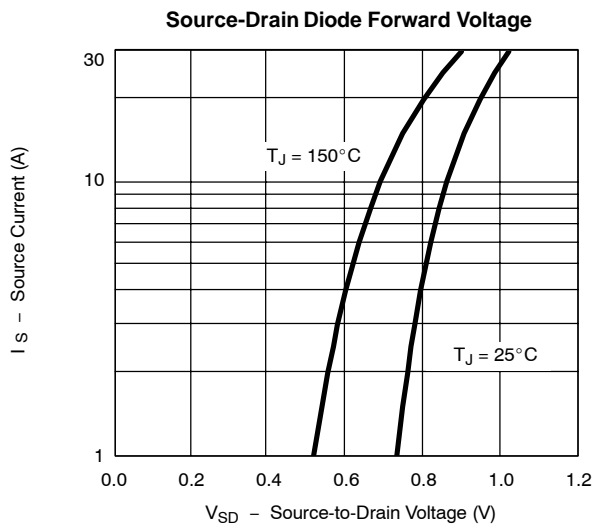
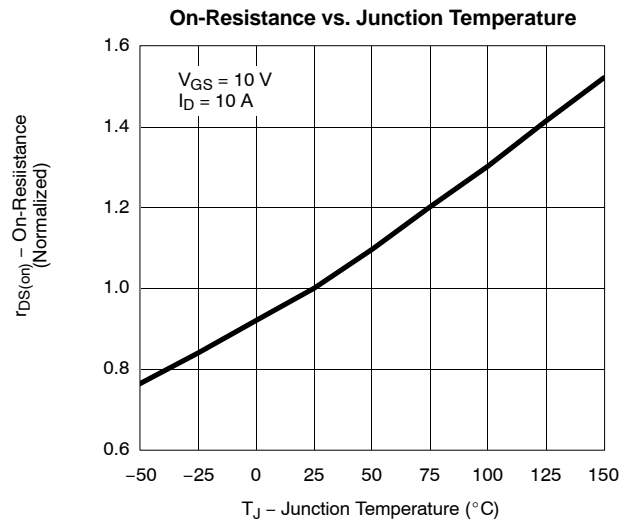
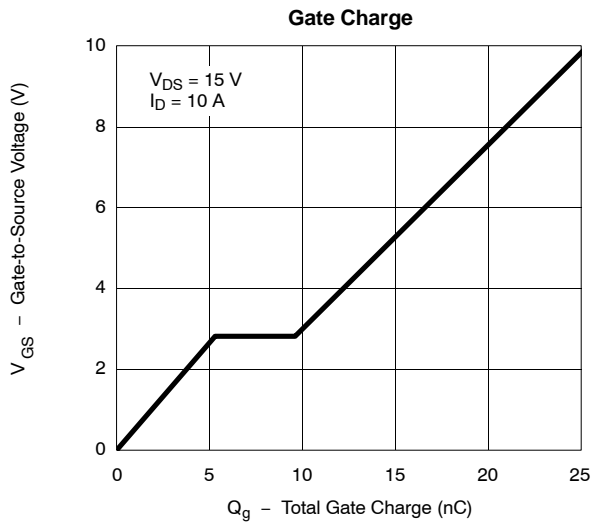


Capacitance



TYPICAL CHARACTERISTICS (25 °C UNLESS NOTED)

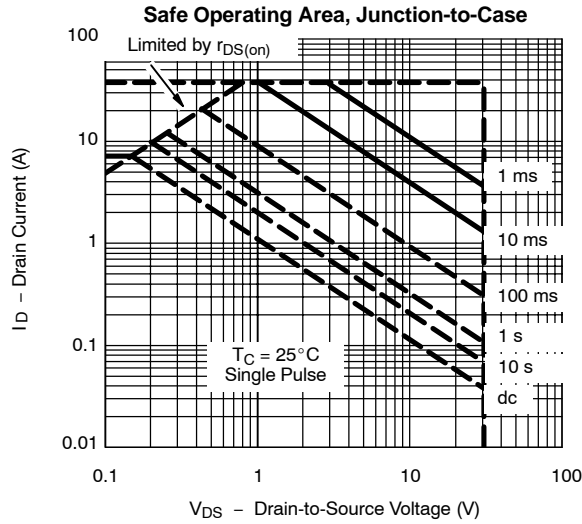
CHANNEL-1



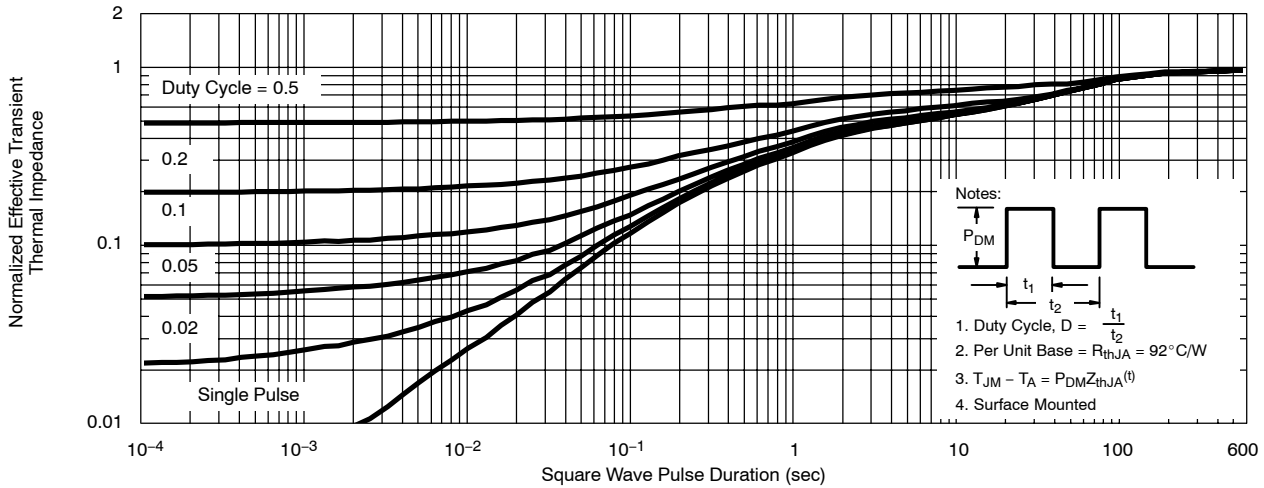


TYPICAL CHARACTERISTICS (25 °C UNLESS NOTED)

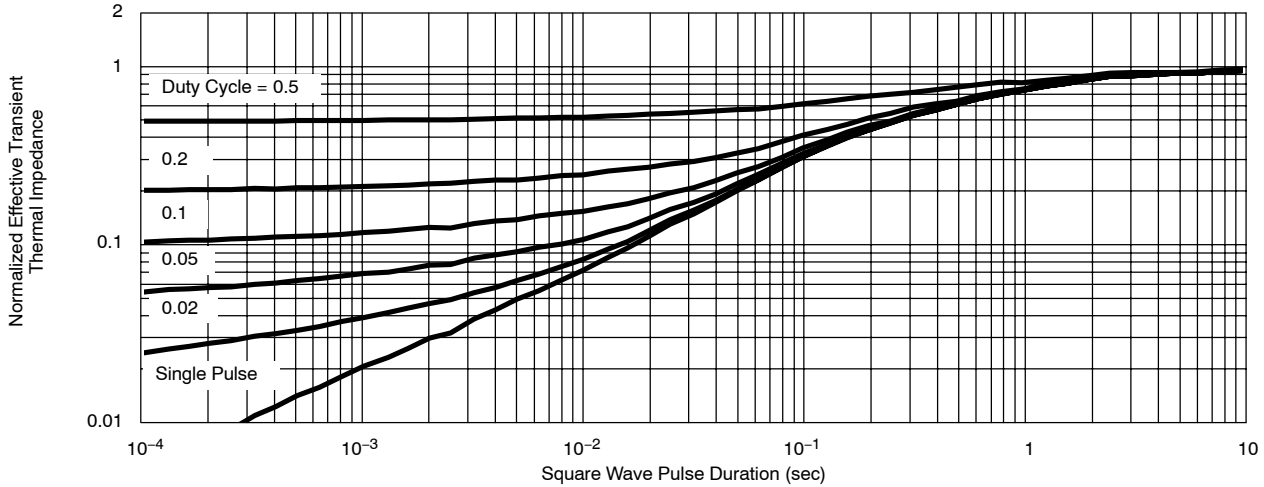
CHANNEL-1



Normalized Thermal Transient Impedance, Junction-to-Ambient



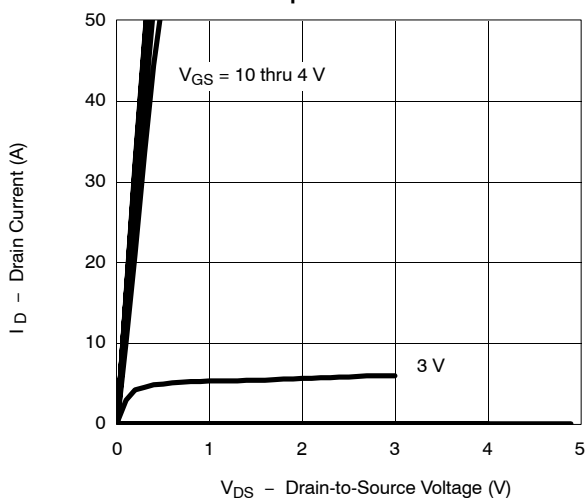
Normalized Thermal Transient Impedance, Junction-to-Foot



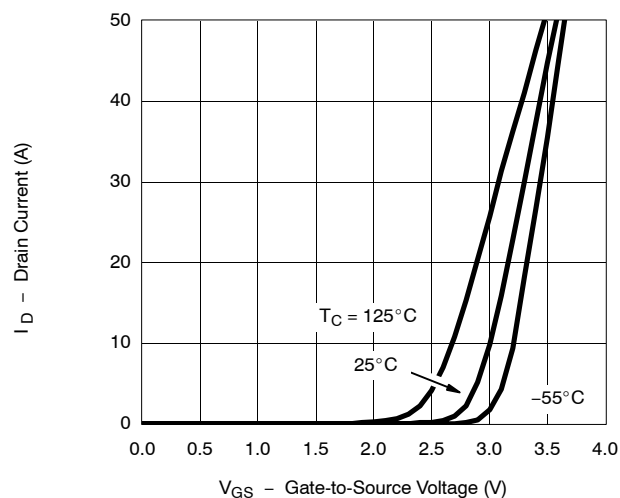
TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

CHANNEL-2

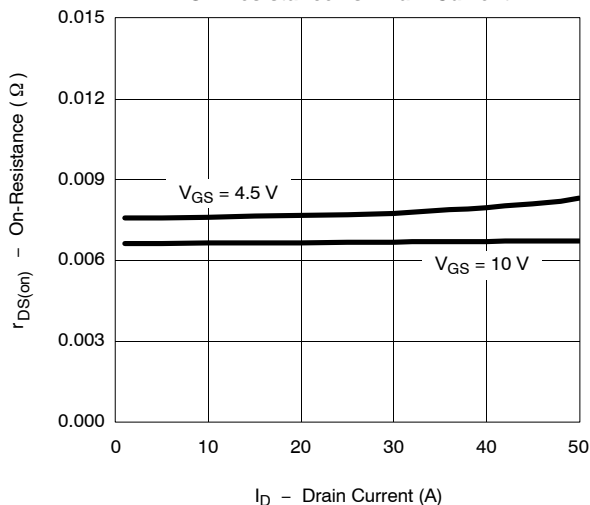
Output Characteristics



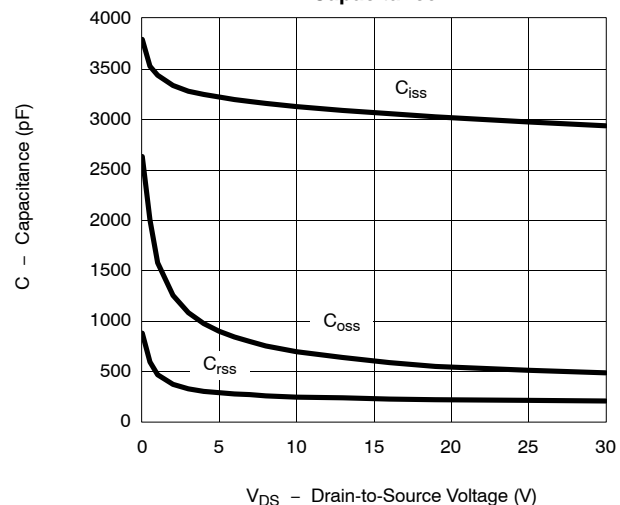
Transfer Characteristics



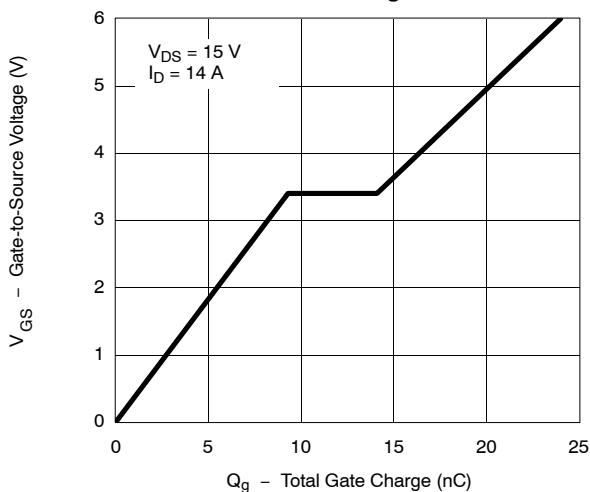
On-Resistance vs. Drain Current



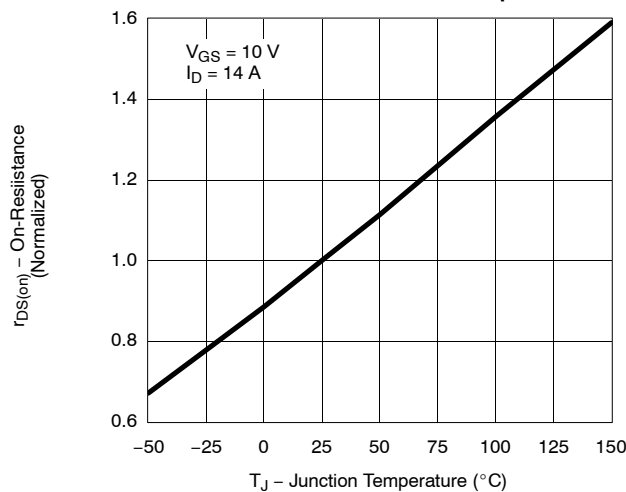
Capacitance



Gate Charge



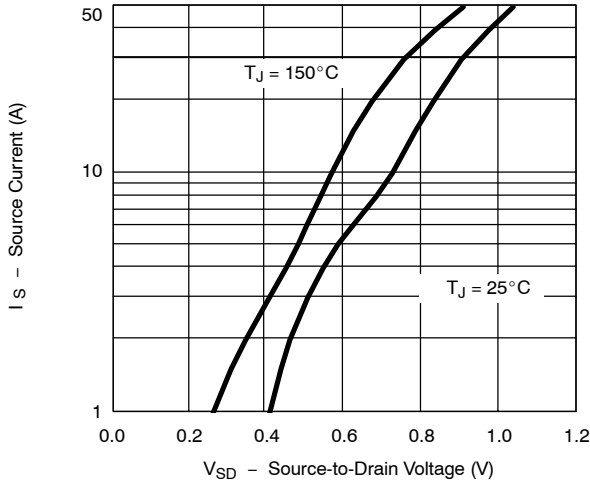
On-Resistance vs. Junction Temperature



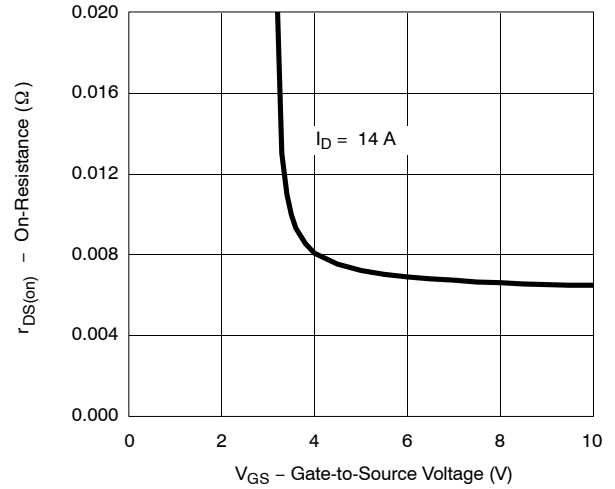


TYPICAL CHARACTERISTICS (25°C UNLESS NOTED) CHANNEL-2

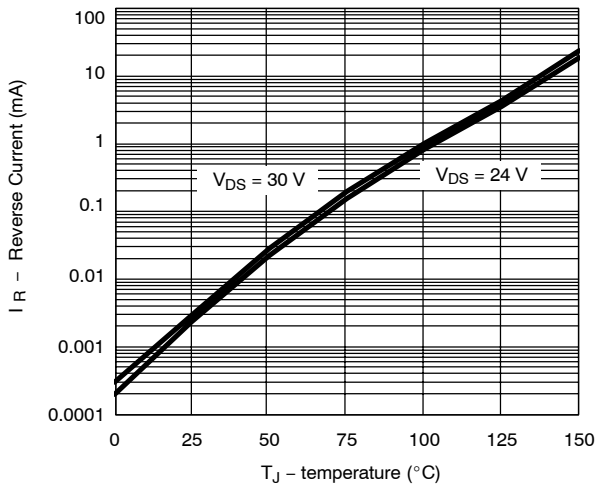
Source-Drain Diode Forward Voltage



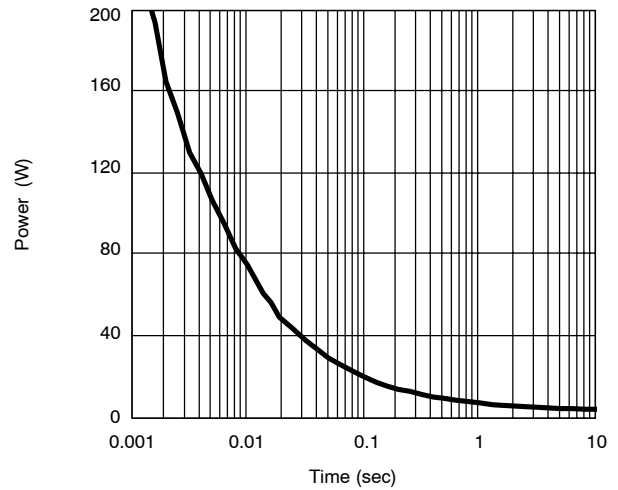
On-Resistance vs. Gate-to-Source Voltage



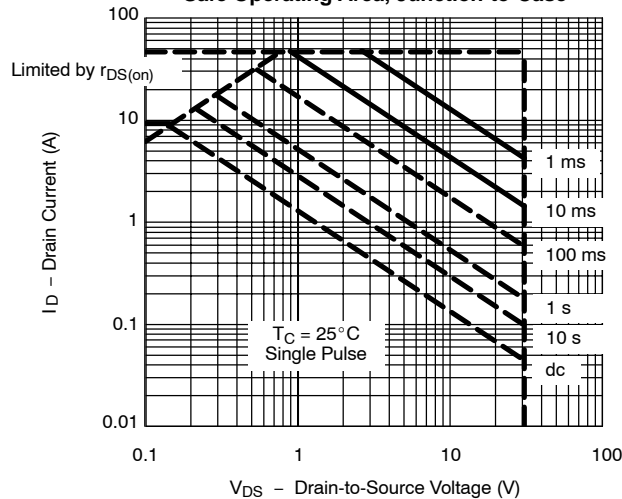
Reverse Current vs. Junction Temperature



Single Pulse Power



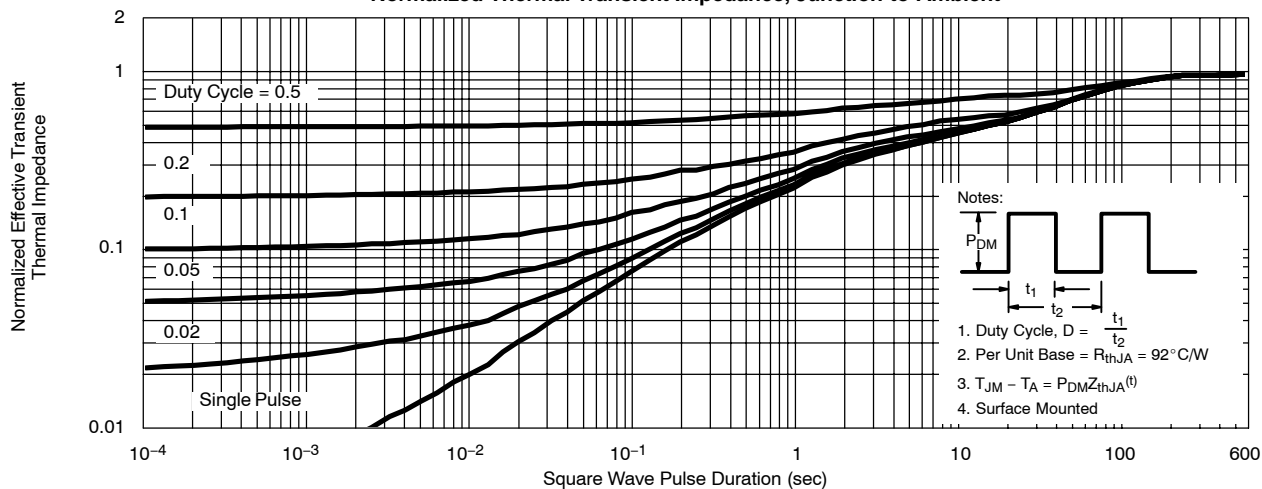
Safe Operating Area, Junction-to-Case



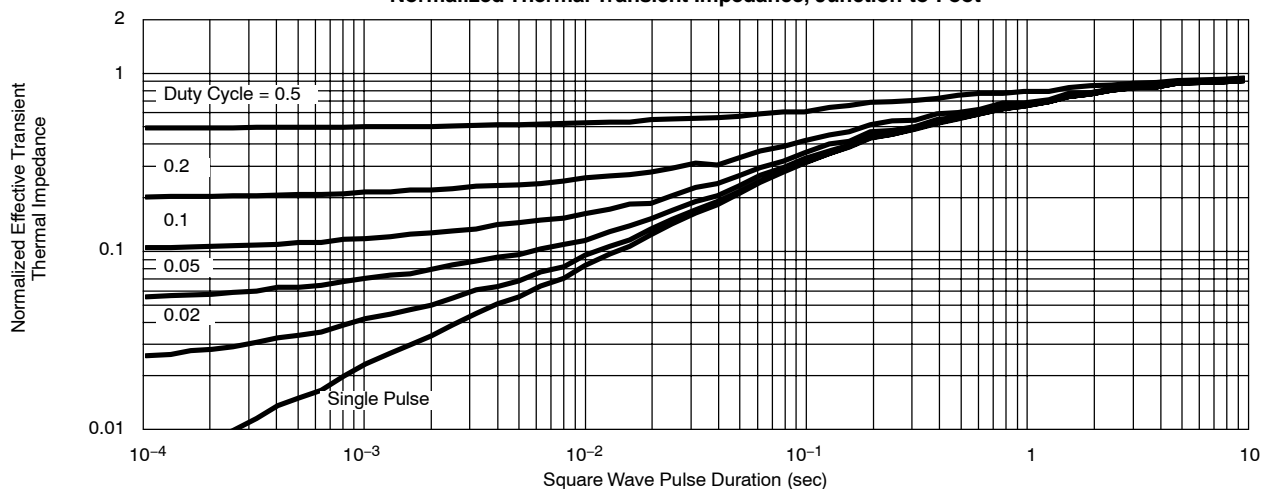
TYPICAL CHARACTERISTICS (25 °C UNLESS NOTED)

CHANNEL-2

Normalized Thermal Transient Impedance, Junction-to-Ambient



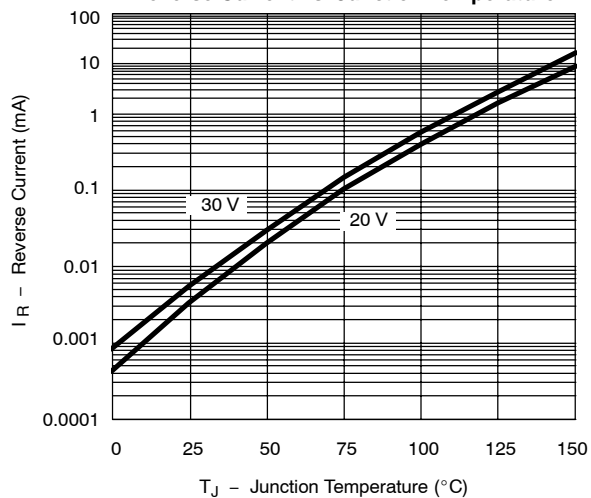
Normalized Thermal Transient Impedance, Junction-to-Foot



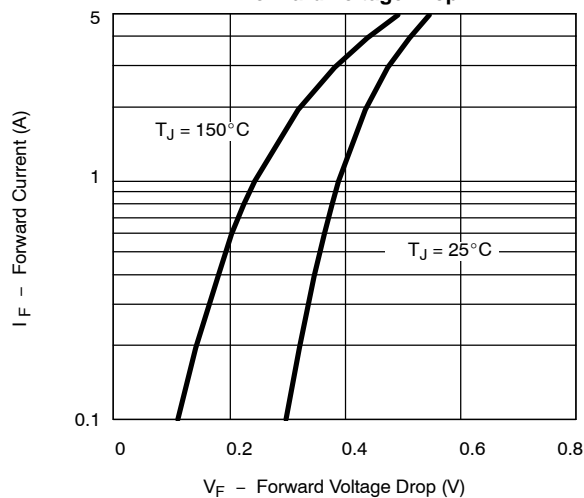
TYPICAL CHARACTERISTICS (25 °C UNLESS NOTED)

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Reverse Current vs. Junction Temperature



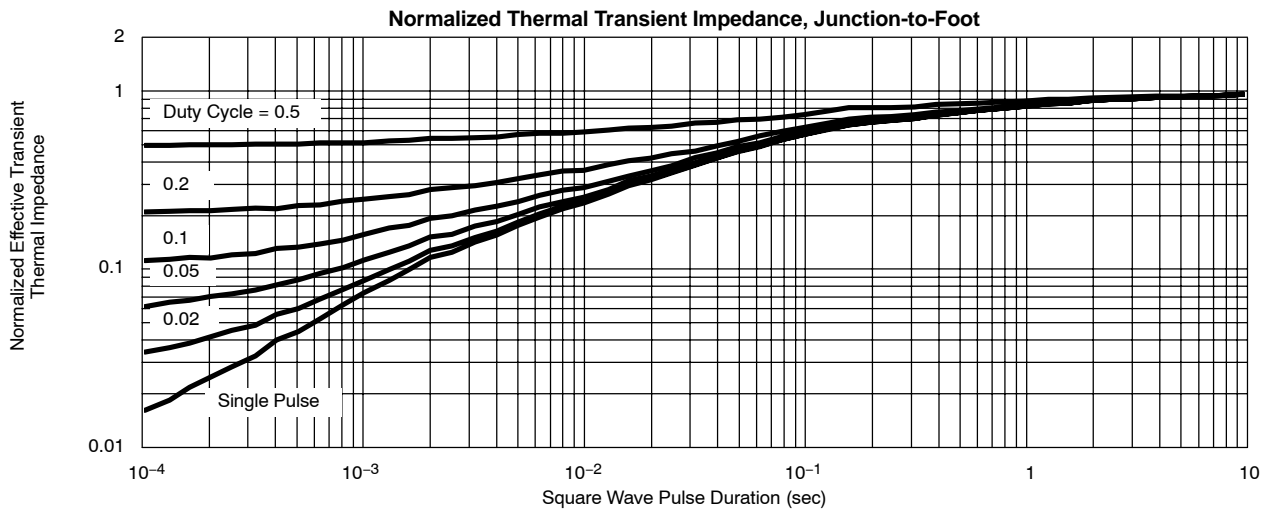
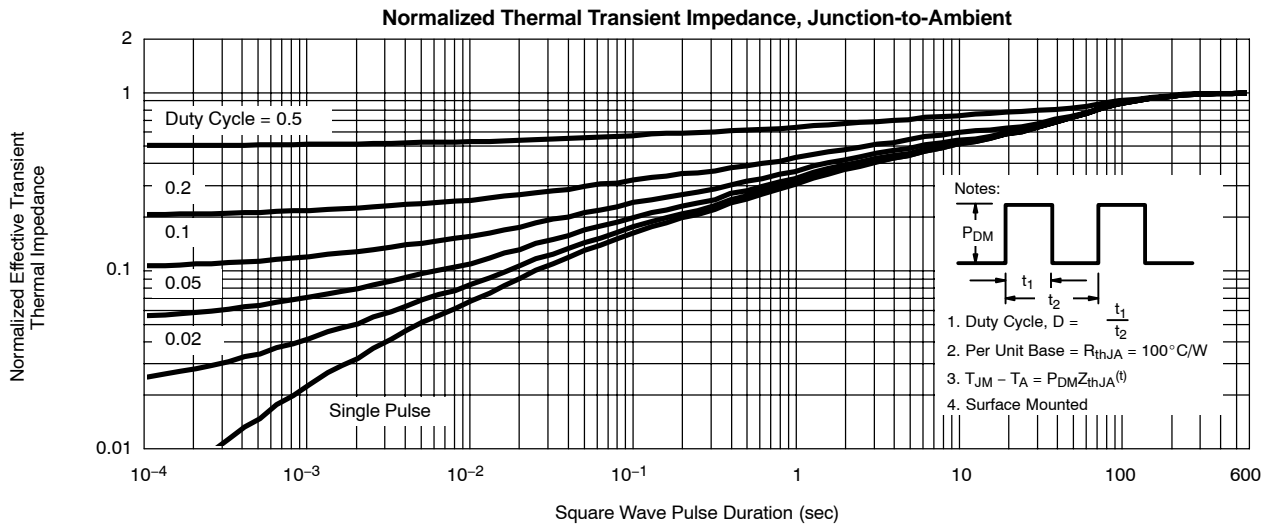
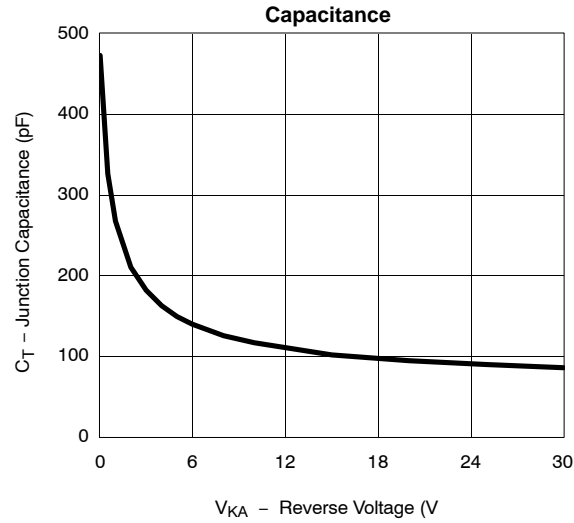
Forward Voltage Drop





TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

SCHOTTKY





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